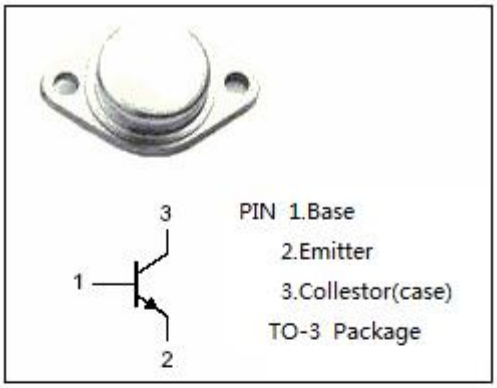
isc Silicon NPN Power Transistor BD116

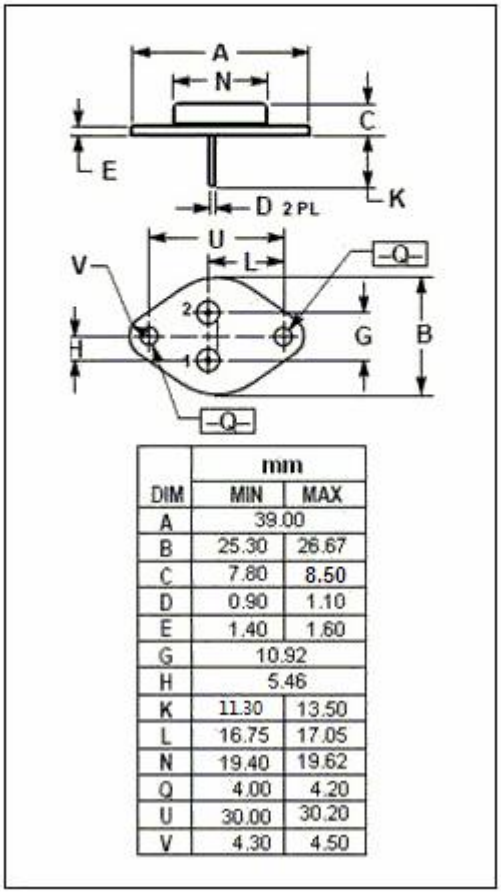
DESCRIPTION

- Excellent Safe Operating Area
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 60V(Min)
- Collector-Emitter Saturation Voltage-
  : $V_{CE(sat)}$= 0.6V(Max)@ I_C = 2A
- Good Linearity of h_{FE}
- Minimum Lot-to-Lot variations for robust device performance and reliable operation.



APPLICATIONS

- Designed for RF power and general-purpose audio amplifier applications



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	3	A
I_{CM}	Collector Current-Peak	5	A
I_B	Base Current-Continuous	1	A
P_C	Collector Power Dissipation@T_C=75℃	15	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 50mA; I_B= 0	60			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 1mA; I_E= 0	80			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 2A; I_B= 0.2A			0.6	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 2A; I_B= 0.2A			1.2	V
I_{CES}	Collector Cutoff Current	V_{CE}= 80V; V_{BE}= 0			0.1	mA
I_{CEO}	Collector Cutoff Current	V_{CE}= 60V; I_B= 0			0.5	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			0.1	mA
h_{FE}	DC Current Gain	I_C= 1A; V_{CE}= 5V	30		200	
h_{FE}	DC Current Gain	I_C= 2A; V_{CE}= 5V	20			
f_T	Current Gain-Bandwidth Product	I_C= 0.5A; V_{CE}= 10V; f=1MHz	30			MHz